

Pf-2801/nec/us/mh

ABSTRACT OF THE DISCLOSURE

A monolithically integrated semiconductor device comprises : a
5 hetero-junction bipolar transistor having at least an electrode contact layer
which contacts directly with at least one of collector, base and emitter
electrodes ; and at least a passive device having at least a passive device
electrode and at least a resistive layer, wherein the electrode contact layer
and the resistive layer comprise the same compound semiconductor layer.

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